International seminar on Nanoscience and Technology- conference proceedings. Sept- 2016 Volume 3, Special Issue - Available Online: http://ijrset.in/Volume3,Special-Issue-II.php Pages: 32-35

ISSN 2394-739X



International Journal for Research in Science Engineering and Technology

## MECHANICAL AND DIELECTRIC STUDIES ON BIS-THIOUREA CADMIUM CHLORIDE (BTCC) CRYSTAL BY SLOW EVAPORATION TECHNIQUE

 <sup>1</sup>R.Ragu, <sup>1</sup>M. Akilan, <sup>1</sup>J.P. Angelena, <sup>2</sup>P. S. Latha Mageshwari, <sup>1</sup>S. Jerome Das <sup>1</sup>Department of Physics, Loyola College, Chennai-34, India
 <sup>2</sup>Department of Physics R. M. K. Engineering College, Kavaraipettai – 601206, India

**ABSTRACT-** Bis-Thiourea Cadmium Chloride is abbreviated as (BTCC) were grown from aqueous solution by low temperature solution growth technique. Good optical quality single crystal of dimensions  $12 \times 7 \times 2.15 \text{ mm}^3$  was harvested in a period of two weeks. Single XRD analysis confirmed that the pure crystal is in orthorhombic structure with lattice parameters a=5.798(Å), b=6.456(Å), c=13.079(Å). FTIR spectroscopy study reveals the presence of functional groups present in the grown crystal. Microhardness studies were carried out using Vickers pyramidal indentation method at room temperature shows that the grown crystal belongs to soft material category. Dielectric studies are done on the grown BTCC crystal

**Keywords-** [Semi organic, Conventional slow evaporation growth technique, Dielectric Studies, NLO material]

## **1. INTRODUCTION**

The rapid developments in the field of optoelectronics necessitates the search for new and efficient nonlinear optical (NLO) materials which can be utilized for optoelectronics applications such as optical computing, optical data storage, optical communications and electro-optic shutters. During the past decade, a number of organic materials with high nonlinear NLO susceptibilities have been synthesized .Recently number of researchers emphasize on the hunt of new semi-organic nonlinear optical materials which exhibit wide transparency region, high damage threshold and high nonlinear coefficient [1-3]. BTCC is a potential NLO candidate which has various applications in the field of laser and opto electronics. The second harmonic

generation (SHG) efficiency of BTCC crystal is 0.73 times greater than urea. The intriguing feature of BTCC is that it has high laser damage threshold and it possess favourable mechanical properties which are comparable with KDP. The powder SHG efficiency of BTCC crystal is 110 times high than quartz [4-6]. In the present investigation Bisthiourea is combined with cadmium chloride to form a crystal and various characterization studies are done on the grown BTCC crystal.

#### **2. MATERIAL SYNTHESIS**

Bis-Thiourea Cadmium Chloride (BTCC) was synthesized by dissipating Thiourea and Cadmium Chloride taken in the ratio of 2:1. The reaction is given below International seminar on Nanoscience and Technology- conference proceedings. Sept- 2016 Volume 3, Special Issue - Available Online: http://ijrset.in/Volume3,Special-Issue-II.php Pages: 32-35

 $Cd[CS(NH_2)_2]_2Cl_2$  (1) Repeated crystallization helps to increase the purity of the synthesized salt. The supersaturated solution of BTCC was kept

 $CdCl_2 + 2CS(NH_2)_2$ 

undisturbed at room temperature. A typical single crystal with size  $12 \times 7 \times 2.15$  mm<sup>3</sup> with in a period of three weeks. The grown crystal is shown in figure 1.



Figure 1- Photograph of Pure BTCC crystals

## **3. RESULTS AND DISCUSSION 3.1. Single Crystal X-ray analysis**

The single crystal X-ray diffraction has been done by using ENRAF NONIUS CAD4 diffractometer with MoK radiation ( = 0.7170 Å) to identify the unit cell dimensions of the grown crystal. The single crystal X-ray diffraction study shows that the grown BTCC crystal is belong to orthorhombic system with space group Pmn2<sub>1</sub>with lattice parameters a = 5.798Å, b = 6.456 Å, c = 13.079 Å and the Volume = 489.6 Å<sup>3</sup>. These values agree well with the reported values [7].

## 3.2. FT-IR Analysis

FT-IR spectra was recorded using JAS-CO FT-IR 460 plus spectrometer using KBr pellet technique in the range 400-4000 cm<sup>-1</sup> to identify the presence of functional group present in the grown crystal. The absorption bands at 3282 and 3389 cm<sup>-1</sup> indicate the presence of N-H symmetric stretching and N-H asymmetric stretching respectively. The absorption band at 1614 cm<sup>-1</sup> indicates the presence functional group  $NH_2$  in the bending mode. The C=S stretching vibrations in the thiourea at 740 and 1417 cm<sup>-1</sup> are shifted to 715 and 1438 cm<sup>-1</sup>, respectively in BTCC which is due to the addition of metal (cadmium) ion in the

complex. The C-N stretching vibrations at 1099 cm<sup>-1</sup> in thiourea are shifted to the higher frequency of 1100 cm<sup>-1</sup>. The band found in BTCC at 1494 cm<sup>-1</sup> corresponds to the 1470 cm<sup>-1</sup> band of thiourea assigned to the H-C-N vibrations.

## **3.3. DIELECTRIC STUDIES**

The dielectric measurements were performed on bisthiourea cadmium chloride single crystals using Hioki Hitester model 3532-50 LCR meter. The dielectric constant and dielectric loss of grown BTCC crystal is shown in Fig 2 & 3 respectively. From the spectrums it is observed that the dielectric constant and dielectric loss decreases slowly with increasing frequency and attains saturation at higher frequencies. The dielectric constant of material is due to the electronic, ionic, dipolar and space charge polarization. The lower value of dielectric constant at higher frequencies is a suitable parameter for the enhancement of SHG. The characteristic of low dielectric loss with high frequency for the sample suggests that the crystal possesses enhanced optical quality with lesser defects and this parameter play a vital role for the construction of devices for non-linear optical materials. Dielectric constant of BTCC crystal is in good agreement with reported value [8]



Figure 2-Dielectric Constant versus log f

#### **3.4. Microhardness Measurements**

Vicker'smicrohardnessstudy was made on the grown BTCC crystal with room temperature by varying the load range using Vicker'smicrohardness tester. The value of Hv is calculated using the following equation

(2) 
$$H_v = 1.8544 P/d^2$$

where P is the applied load in g, d is the diagonal length in mm and  $H_v$  in kg/mm<sup>2</sup>. The variation of Hv with the applied load of BTCC crystal is shown in Fig 5. A plot of log d vs log P is shown in Fig 6. The plot of log d Vs log P yields a straight line and the slope gives the work hardening coefficient 'n'. The value of n is 3.5 and it is more than 2 so it is soft material [9].

The Mayer's index number was calculated from Mayer's law, which relates load and indentation diagonal length. According to Meyer's relation

# $P=K_1d^n$ (3)

Where  $K_1$  is the standard hardness value which can be found out from the plot P versus  $d^n$ .

The material takes some time to revert to the elastic mode after every indentation a correction 'n' is applied to the d value.



Figure 3- Dielectric Loss versus log f

Kick's law is related as  $P=K_2 (d+x)^2$ (4)

From 3 and 4 equations

$$d^{n/2} = (K_2/K_1)^{1/2}d + (K_2/K_1)x$$

The slope of  $d^{n/2}$  versus d yield  $(K_2/K_1)^{1/2}$ and the intercept is a measure of x. The fracture toughness  $K_c$  is given by  $K_c=P/c^{3/2}$ 

(6)

Where c is the crack length measured from the centre of the indentation mark to crack tip. P is the applied load and geometrical constant =7 for Vickers indenter.

The yield strength (v) of the material can be found out using the relation

$$v^{-\frac{H_{v}}{2.9}} \{1 - (n-2)\} \left[\frac{12.5(n-2)}{1 - (n-2)}\right]^{n-2}$$
(7)

The elastic stiffness constant  $(C_{11})$  was calculated using the formula [10]

Wooster empricial relation  $C_{11} = (Hv)^{7/4}$  (8) There are two factors important in determining the value of  $C_{11}$ . The first factor is tightness of bonding between the neighbouring atoms. The second factor is rate of variation with position of the atoms of the forces of attraction and repulsion between them. Stiffness constant increases with increase of load.

Parameters	Values for BTCC
Ν	3.5
K <sub>1</sub> (kg/mm)	36.62 x 10 <sup>-3</sup>
K <sub>2</sub> (kg/mm)	7.49 x 10 <sup>-3</sup>
$H_v(kg/mm^2)$	54.53
<sub>v</sub> (M a)	1.723
$C_{11}(10^{14} \text{ Pa})$	19.460

Table 1- Various Parameters calculated using Microhardness study for BTCC crystal

## **CONCLUSION**

BTCC has been grown by slow evaporation technique and have achieved good quality optical crystal. Single crystal X-ray Diffraction study reveals that the grown crystal comes under orthorhombic system with space group Pmn2<sub>1</sub>. The presence of the functional group is revealed by FTIR spectroscopic study. From Dielectric study it is observed that the dielectric constant and dielectric loss decreases slowly with increasing frequency and attains saturation at higher frequencies. The load dependent hardness parameters are calculated using microhardness study

#### ACKNOWLEDGEMENT

The authors are thankful to Loyola College – Times of India Major Research project (3LCTOI14PHY002)

## REFERENCES

[1]. S. Dhanuskodi, P. A. Angeli Mary, J. Cryst. Growth, 253, (2008), 424-428.

[2]. J. N. Woodford, C. H. Wang, Y Jen Alex K, Chem. Phys. 271, (2001), 137

[3]. K. Ambujam, K. Rajarajan, S. Selvakumar, A. Joseph, P. Sagayaraj, J. Cryt. Growth, 286, 440

[4]. Bincy Susan Samuel, R. Krishnamurthy, R. Rajasekaran, SpectrochimicaActaPart . A: Molecular and Bimolecular Spectroscopy, 2014, Pages: 526-532.

[5]. A.PricillaJeyakumari,, J. Ramajothi, S. Dhanuskodi, J. Cryst. Growth, 269 (2004) 558-564.

[6]. Xing Guangcai, Jiang Minhua, Shao Zongshu, Xu Dong, Chin. J. Lasers (1987) 302

[7]. V. Venkatramanan, C. K. Subramanian, H. L. Bhat, J. Appl. Phys. 77, 6049, (1995).

[8]. R. Uthrakumar, C. Vesta, C. Justin Raj, Rani Christhu Das, S. Jerome Das, Cryst. Res. Technol., 43, (2008), Pages: 428-432.
[9]. Shakir M, Ganesh V, Wahab MA,

Bhagavannarayana G, Kishan Rao K, Mater SciEng B, 172 (2010), 9-14.

[10]. W. A. Wooster, Rep. Progr. Phys., 16, 62 (1953)